

---

# 2SA1374

Silicon PNP Epitaxial

# HITACHI

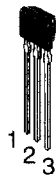
---

## Application

Low frequency amplifier

## Outline

SPAK



1. Emitter
2. Collector
3. Base

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-55	V
Collector to emitter voltage	$V_{CEO}$	-55	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Base current	$I_B$	-30	mA
Collector power dissipation	$P_C$	300	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-55	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-55	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-0.1	$\mu A$	$V_{CB} = -18 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.05	$\mu A$	$V_{EB} = -2 \text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE}^{*1}$	160	—	500		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	-0.66	-0.75	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.1	-0.5	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Gain bandwidth product	$f_T$	—	250	—	MHz	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	2.5	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SA1374 is grouped by  $h_{FE}$  as follows.

C	D
160 to 320	250 to 500

See characteristic curves of 2SA836.

